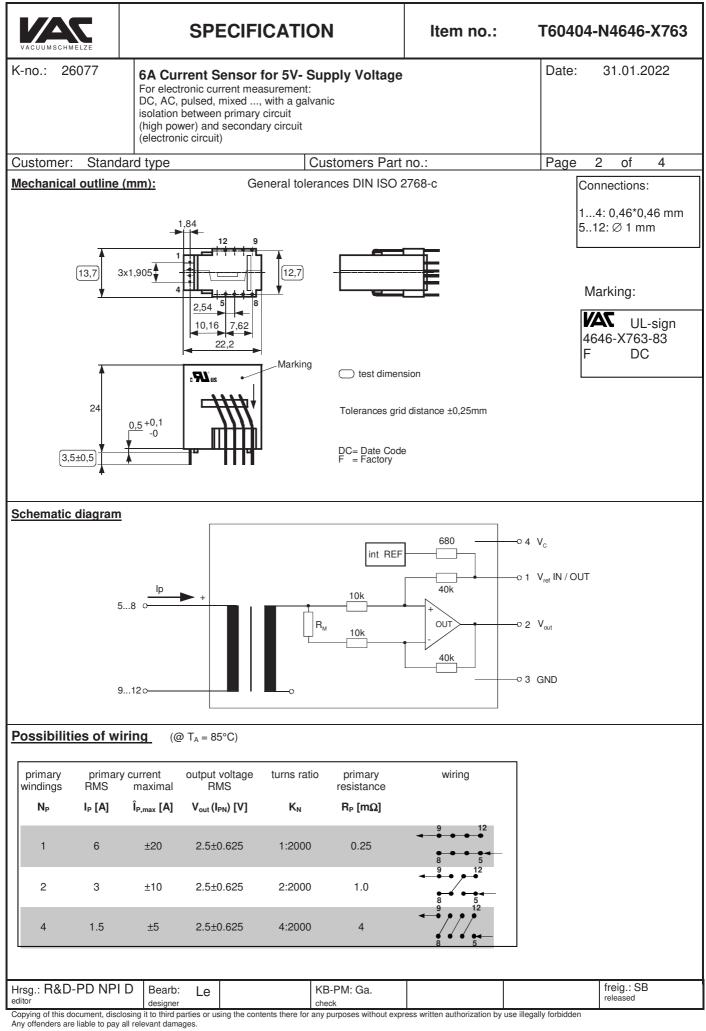
K-no.: 26077 Customer: Stanc	6A Current Sensor for 5V- Supply Vol For electronic current measurement:	I			
Customer: Stand	DC, AC, pulsed, mixed, with a galvanic isolation between primary circuit (high power) and secondary circuit (electronic circuit)	Date:	Date: 31.01.2022		
	dard type Customers	Part no.:		Page	1 of 4
Description Closed loop (compective Current Sensor with field probe Printed circuit boarce Casing and materia	Characteristics ensation) • Excellent accuracy magnetic • Very low offset current • Very low temperature dependency • Very low temperature dependency I mounting • current drift	Ma apr y and offset •	AC variab drives Static con Battery su Switched Power Su	stationary opera	ation in industrial and servo motor notor drives ons pplies (SMPS) g applications
Electrical data – Ra	atinas				
IPN	Primary nominal r.m.s. current		6		А
Vout	Output voltage @ IP		-	ef ± (0.625*1P/1	
Vout	Output voltage @ I _P =0, T _A =25°C			ef ± 0.0056	V
V _{Ref}	External Reference voltage range		0		V
• 1101	Internal Reference voltage			5 ± 0.005	V
KN	Turns ratio			.4 : 2000	v
T XIN	Turis fallo		1	.4.2000	
<u> Accuracy – Dynam</u>	ic performance data				
		min.	typ.	max.	Unit
I _{P,max} X	Max. measuring range Accuracy @ I _{PN} , T _A = 25°C	±20		0.7	%
Λ	-			0.7	70
0.				0.1	0/
EL V-	Linearity			0.1	%
V _{out} - V _{Ref}	Offset voltage @ I _P =0, T _A = 25°C	T 40 0500	0	±5.3	mV
V _{out} - V _{Ref} ΔV _o / V _{Ref} / ΔT	Offset voltage @ I _P =0, T _A = 25°C Temperature drift of V _{out} @ I _P =0, V _{Ref} =2,5V,	T _A = -4085°C	6	-	mV ppm/°C
V _{out} - V _{Ref} ΔV _o / V _{Ref} / ΔT t _r	Offset voltage @ I _P =0, T _A = 25°C Temperature drift of V _{out} @ I _P =0, V _{Ref} =2,5V, Response time @ 90% von I _{PN}	T _A = -4085°C	300	±5.3	mV ppm/°C ns
V _{out} - V _{Ref} ΔV _o / V _{Ref} / ΔT tr Δt (I _{P,max})	Offset voltage @ I _P =0, T _A = 25°C Temperature drift of V _{out} @ I _P =0, V _{Ref} =2,5V, Response time @ 90% von I _{PN} Delay time at di/dt = 100 A/μs		-	±5.3	mV ppm/°C ns ns
V _{out} - V _{Ref} ΔV _o / V _{Ref} / ΔT tr Δt (I _{P,max}) f	Offset voltage @ I _P =0, T _A = 25°C Temperature drift of V _{out} @ I _P =0, V _{Ref} =2,5V, Response time @ 90% von I _{PN}	T _A = -4085°C DC200	300	±5.3	mV ppm/°C ns
V _{out} - V _{Ref} ΔV _o / V _{Ref} / ΔT tr Δt (I _{P,max}) f	Offset voltage @ I _P =0, T _A = 25°C Temperature drift of V _{out} @ I _P =0, V _{Ref} =2,5V, Response time @ 90% von I _{PN} Delay time at di/dt = 100 A/μs	DC200	300 200	±5.3 30	mV ppm/°C ns ns kHz
V _{out} - V _{Ref} ΔV _o / V _{Ref} / ΔT tr Δt (I _{P,max}) f <u>General data</u>	Offset voltage @ I _P =0, T _A = 25°C Temperature drift of V _{out} @ I _P =0, V _{Ref} =2,5V, Response time @ 90% von I _{PN} Delay time at di/dt = 100 A/μs Frequency bandwidth	DC200 <mark>min.</mark>	300	±5.3 30 max.	mV ppm/°C ns ns kHz Unit
V _{out} - V _{Ref} ΔV _o / V _{Ref} / ΔT tr Δt (I _{P,max}) f General data TA	Offset voltage @ I _P =0, T _A = 25°C Temperature drift of V _{out} @ I _P =0, V _{Ref} =2,5V, Response time @ 90% von I _{PN} Delay time at di/dt = 100 A/μs Frequency bandwidth	DC200 <mark>min.</mark> -40	300 200	±5.3 30 max. +85	mV ppm/°C ns ns kHz Unit °C
V _{out} - V _{Ref} ΔV _o / V _{Ref} / ΔT tr Δt (I _{P,max}) f General data T _A T _S	 Offset voltage @ I_P=0, T_A= 25°C Temperature drift of V_{out} @ I_P=0, V_{Ref} =2,5V, 7 Response time @ 90% von I_{PN} Delay time at di/dt = 100 A/µs Frequency bandwidth Ambient operating temperature Ambient storage temperature 	DC200 <mark>min.</mark>	300 200 typ.	±5.3 30 max.	mV ppm/°C ns ns kHz Unit °C °C
V _{out} - V _{Ref} ΔV _o / V _{Ref} / ΔT tr Δt (I _{P,max}) f Ceneral data T _A T _S m	 Offset voltage @ I_P=0, T_A= 25°C Temperature drift of V_{out} @ I_P=0, V_{Ref} =2,5V, Response time @ 90% von I_{PN} Delay time at di/dt = 100 A/µs Frequency bandwidth Ambient operating temperature Ambient storage temperature Mass 	DC200 <mark>min.</mark> -40 -40	300 200 typ. 12	±5.3 30 max. +85 +105	mV ppm/°C ns ns kHz Unit °C °C g
$V_{out} - V_{Ref}$ $\Delta V_o / V_{Ref} / \Delta T$ tr $\Delta t (I_{P,max})$ f $\Delta t (I_{P,max})$ TA Ts M Vc	 Offset voltage @ I_P=0, T_A= 25°C Temperature drift of V_{out} @ I_P=0, V_{Ref} =2,5V, 7 Response time @ 90% von I_{PN} Delay time at di/dt = 100 A/µs Frequency bandwidth Ambient operating temperature Ambient storage temperature Mass Supply voltage 	DC200 <mark>min.</mark> -40	300 200 typ. 12 5	±5.3 30 max. +85	mV ppm/°C ns ns kHz Unit °C °C °C g V
$V_{out} - V_{Ref}$ $\Delta V_o / V_{Ref} / \Delta T$ tr $\Delta t (I_{P,max})$ f General data TA Ts m Vc Ic	 Offset voltage @ I_P=0, T_A= 25°C Temperature drift of V_{out} @ I_P=0, V_{Ref} =2,5V, Response time @ 90% von I_{PN} Delay time at di/dt = 100 A/µs Frequency bandwidth Ambient operating temperature Ambient storage temperature Mass Supply voltage Current consumption Constructed and manufactored and tested in Reinforced insulation, Insulation material grout 	DC200 min. -40 -40 4.75 accordance with up 1, Pollution de	300 200 typ. 12 5 15 EN 61800	±5.3 30 max. +85 +105 5.25	mV ppm/°C ns ns kHz Unit °C °C °C g V v mA
V _{out} - V _{Ref} ΔV _o / V _{Ref} / ΔT tr Δt (I _{P,max}) f General data Ta Ts m Vc Ic Sclear	 Offset voltage @ I_P=0, T_A= 25°C Temperature drift of V_{out} @ I_P=0, V_{Ref} =2,5V, Response time @ 90% von I_{PN} Delay time at di/dt = 100 A/µs Frequency bandwidth Ambient operating temperature Ambient storage temperature Mass Supply voltage Current consumption Constructed and manufactored and tested in Reinforced insulation, Insulation material grout Clearance (component without solder pad) 	DC200 min. -40 -40 4.75 accordance with up 1, Pollution de 9.6	300 200 typ. 12 5 15 EN 61800	±5.3 30 max. +85 +105 5.25	mV ppm/°C ns ns kHz Unit °C °C °C g V mA to Pin 5 – 12) mm
V _{out} - V _{Ref} ΔV _o / V _{Ref} / ΔT tr Δt (I _{P,max}) f General data Ta Ta Ts m Vc Ic Ic	 Offset voltage @ I_P=0, T_A= 25°C Temperature drift of V_{out} @ I_P=0, V_{Ref} =2,5V, Response time @ 90% von I_{PN} Delay time at di/dt = 100 A/µs Frequency bandwidth Ambient operating temperature Ambient storage temperature Mass Supply voltage Current consumption Constructed and manufactored and tested in Reinforced insulation, Insulation material grout 	DC200 min. -40 -40 4.75 accordance with up 1, Pollution de	300 200 typ. 12 5 15 EN 61800	±5.3 30 max. +85 +105 5.25	mV ppm/°C ns ns kHz Unit °C °C °C g V v mA
V _{out} - V _{Ref} ΔV _o / V _{Ref} / ΔT tr Δt (I _{P,max}) f General data Ta Ta Ts m Vc Ic Ic	 Offset voltage @ I_P=0, T_A= 25°C Temperature drift of V_{out} @ I_P=0, V_{Ref} =2,5V, Tesponse time @ 90% von I_{PN} Delay time at di/dt = 100 A/µs Frequency bandwidth Ambient operating temperature Ambient storage temperature Mass Supply voltage Current consumption Constructed and manufactored and tested in Reinforced insulation, Insulation material grout Clearance (component without solder pad) Creepage (component without solder pad) 	DC200 min. -40 -40 4.75 accordance with up 1, Pollution de 9.6 10.6	300 200 typ. 12 5 15 EN 61800 egree 2	±5.3 30 max. +85 +105 5.25 -5-1 (Pin 1 – 4 t	mV ppm/°C ns ns kHz Unit °C °C °C g V mA to Pin 5 – 12) mm mm



VACUUMSCHMELZE	SPECIFICATION Item no.:		T60404-	T60404-N4646-X763		
K-no.: 26077	6A Current Sensor for 5V- Supply Voltage For electronic current measurement: DC, AC, pulsed, mixed, with a galvanic isolation between primary circuit (high power) and secondary circuit (electronic circuit)			Date:	Date: 31.01.2022	
Customer: Stand	dard type	ard type Customers Part no.:				
Electrical Data						
	N4		<mark>min. typ.</mark>	max.	Unit	
VCtot		upply voltage (without function)	15m A . I. *K	7 V ./P:	V mA	
		ent with primary current	15mA +lp*KN+	- Vout/ FL		
lout,SC		t output current	±20		mA	
R _P		/ primary winding @ T _A =25°C	1		mΩ	
Rs		coil resistance @ T _A =85°C		67	Ω	
R _{i,Ref}		stance of Reference input	670		Ω	
Ri,(Vout)	•	stance of Vout		1	Ω	
RL	External rec	commended resistance of Vout	1		kΩ	
CL	External rec	commended capacitance of Vout		500	pF	
$\Delta X_{Ti} / \Delta T$	Temperatur	e drift of X @ T _A = -40 +85 °C		40	ppm/K	
$\Delta V_0 = \Delta (V_{out} - V_{Ref})$	Sum of any	offset drift including:	5	15	mV	
V _{0t}	Longtermdr	ift of V ₀	3		mV	
V _{0T}	•	e drift von V ₀ @ T _A = -40+85°C	3		mV	
Vон		of Vout @ IP=0 (after an overload of 10	x I _{PN})	7.5	mV	
$\Delta V_0 / \Delta V_C$	-	age rejection ratio		1	mV/V	
V _{oss}		(with 1 MHz- filter first order)		55	mV	
Voss		(with 100 kHz- filter first order)	9	15	mV	
Voss		(with 20 kHz- filter first order)	2.5	4	mV	
Ck		ossible coupling capacity (primary -		10	pF	
		stress according to M3209/3 - 2000 Hz, 1 min/Oktave, 2 hours		30	g	
	ement after temp	erature balance of the samples at room	temperature; SC = signifi	cant characteristic)		
V _{out} (V	') M3011/6:	Output voltage		625±0,7%	mV (SC)	
V _{out} -V _{Ref} (V	,	Offset voltage		± 5.3	mV	
V _d (V) M3014:	Test voltage, 1 s		1.8	kV	
V _e (A	QL 1/S4)	pin 1 – 4 vs. pin 5 – 12 Partial discharge voltage acc.M302	24	1400	VRMS	
ve (//		with V_{vor}	-7	1750		
Type Testing (Pin 1	- 4 to Pin 5 - 12)				
Vw		t test according to M3064 (1,2 μs / ! pol. +, 5 pulses -> pol	50 µs-wave form)	8	kV	
V _d		age to M3014	(5 s)	3.6	kV _{RMS}	
Ve	Partial disch	narge voltage acc.M3024	· · · ·	1400	VRMS	
Further standards Operating temperature The color of the plasti	sitive output volta UL 508 file E31 of the current se c material is not s	age appears at point V _{OUT} , by primary cL 7483, category NMTR2 / NMTR8 ensor and the primary conductor must no specified and the current sensor can be has no effect on the specifications or UL	ot exceed 105°C. supplied in different color		Vrms	
Hrsg.: R&D-PD NP	ID Bearb:	Le KB-PM: Ga.			freig.: SB	

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VACUUMSCH	MELZE	SPE	CIFICATION	Item no.:	T60404-N4646-X763
K-no.: 2	26077	For electronic curre	ixed, with a galvanic primary circuit	age	Date: 31.01.2022
Custome	r: Standa	ard type	Customers F	Part no.:	Page 4 of 4
Explanation	on of seve	ral of the terms us	ed in the tablets (in alphabe	etical order)	
t _r :			e dynamic performance for the ectangular current and the out		ange), measured as delay time
$\Delta t (I_{Pmax}):$			namic performance for the rap d the output voltage V _{out} (I _{Pmax})		
V ₀ :		ltage between V _{out} (0) - 2,5V	and the rated reference voltag	ge of $V_{ref} = 2,5V.$	
Upd	Rated disc UPD	tharge voltage (recu = $\sqrt{2} * V_e / 1,5$	rring peak voltage separated	by the insulation) proved v	with a sinusoidal voltage $V_{\mbox{\scriptsize e}}$
Vvor		ltage is the RMS va 61800-5-1 = 1,875 *Upp / √2	alve of a sinusoidal voltage wi	th peak value of 1,875 * U	PD required for partial discharge
Vsys	System vo	ltage RMS valu	e of rated voltage according t	o IEC 61800-5-1	
Vwork	Working ve	oltage voltage ac	cording to IEC 61800-5-1 whi	ch occurs by design in a c	ircuit or across insulation
V _{0H} :	Zero var	iation of V _o after ove	erloading with a DC of tenfold	the rated value	
V _{0t} :	Long teri	m drift of V $_{\circ}$ after 10	0 temperature cycles in the ra	ange -40 bis 85 °C.	
X:		ble measurement e $00 \cdot \left \frac{V_{out}(I_{PN}) - 0}{0,625} \right $	rror in the final inspection at F $rac{V_{out}(0)}{V} - 1 \Biggl $ %	RT, defined by	
Xges(IPN):			rror including any drifts over the $\frac{W}{2} - 1 \mid \% \text{ or } X_{\text{ges}} = 100$		
ε∟:	Linearity	fault defined by	$\varepsilon_{\rm L} = 100 \cdot \left \frac{\rm I_{\rm P}}{\rm I_{\rm PN}} - \frac{\rm V_{out}(I_{\rm P})}{\rm V_{out}(I_{\rm PN})} \right $	$\frac{\left -V_{out}(0)\right }{\left -V_{out}(0)\right } \ll$	
	D-PD NPI	D Bearb: Le	KB-PM: Ga.		freig.: SB

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